

# BUK762R9-40E,118-VB Datasheet

## N-Channel 40 V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a, c</sup>	$Q_g$ (Typ.)
40	0.0017 at $V_{GS} = 10$ V	150	120 nC
	0.0025 at $V_{GS} = 4.5$ V	135	

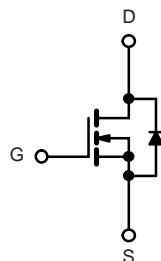
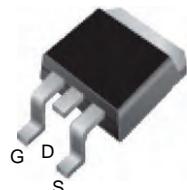
### FEATURES

- Trench Power MOSFET
- 100 %  $R_g$  and UIS Tested



### APPLICATIONS

- Synchronous Rectification
- Power Supplies

D<sup>2</sup>PAK (TO-263)

N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	150 <sup>a, c</sup>	A
		120 <sup>c</sup>	
		29 <sup>b</sup>	
		23 <sup>b</sup>	
	$I_{DM}$	380	
Pulsed Drain Current	$I_{AS}$	80	
Avalanche Current Pulse	$E_{AS}$	320	mJ
Continuous Source-Drain Diode Current	$I_S$	110 <sup>a, c</sup>	A
		2.6 <sup>b</sup>	
Maximum Power Dissipation	$P_D$	312 <sup>a</sup>	W
		200	
		3.13 <sup>b</sup>	
		2.0 <sup>b</sup>	
	$T_J, T_{stg}$	-55 to 150	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	32	40	°C/W
Maximum Junction-to-Case	$R_{thJC}$	0.33	0.4	

Notes:

a. Based on  $T_C = 25$  °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. Calculated based on maximum junction temperature. Package limitation current is 110 A.

**SPECIFICATIONS**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

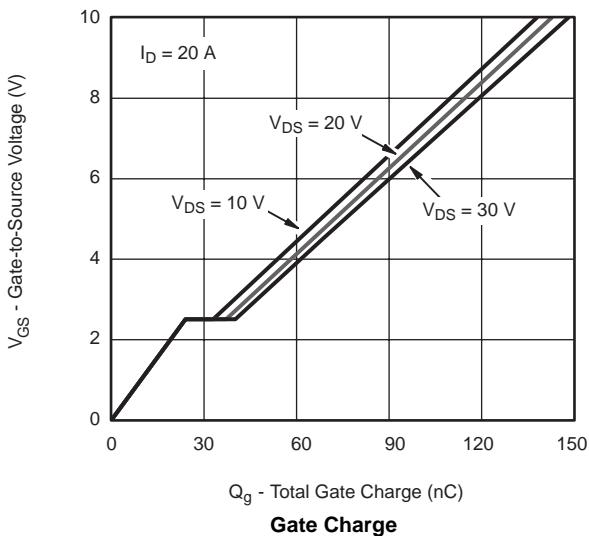
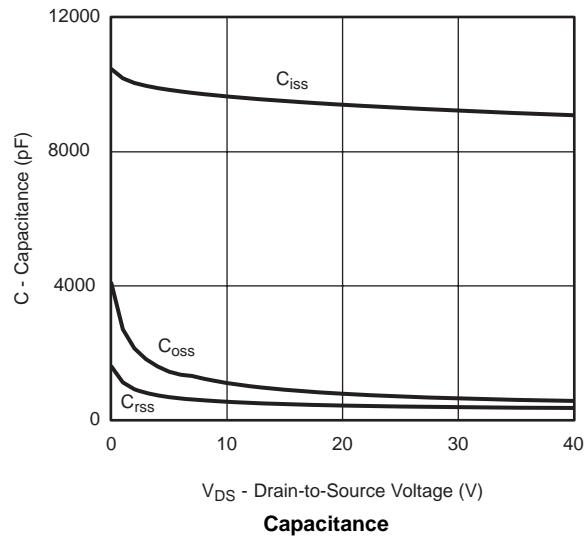
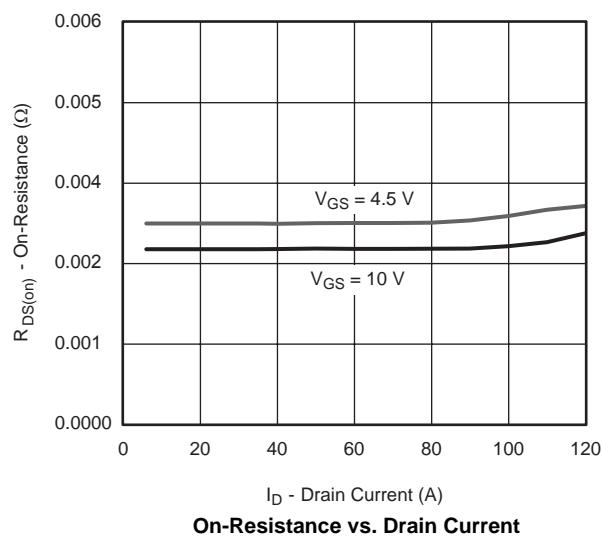
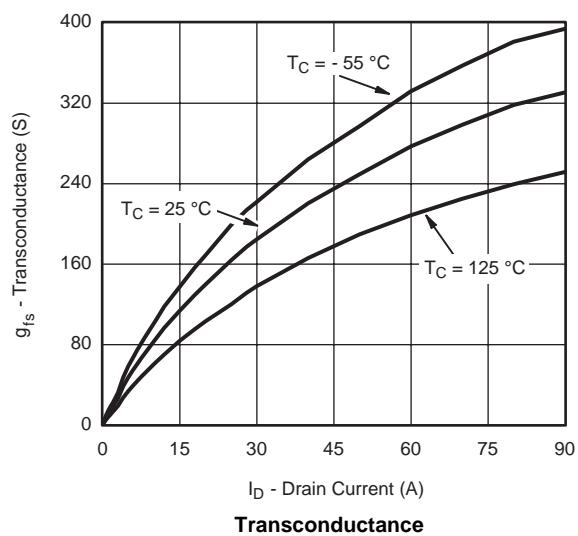
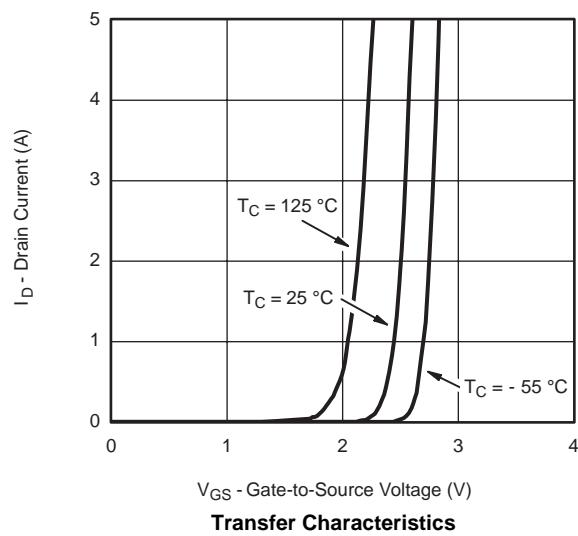
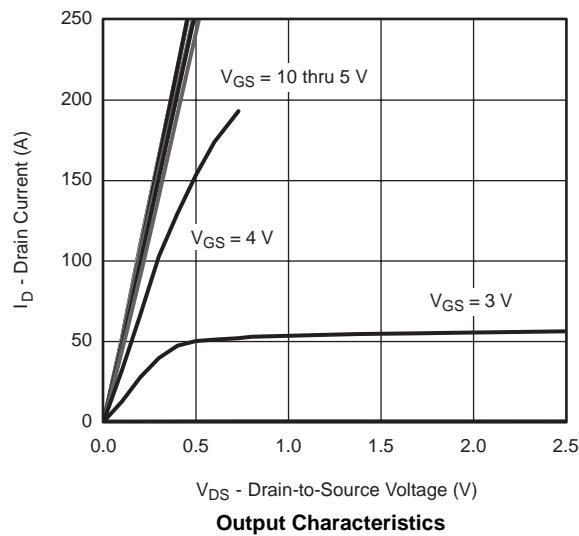
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	45			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		41		mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			-8		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1.2		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$		0.0017		Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0025		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$		180		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		9000		pF
Output Capacitance	$C_{oss}$			650		
Reverse Transfer Capacitance	$C_{rss}$			450		
Total Gate Charge	$Q_g$	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		120	180	nC
Gate-Source Charge	$Q_{gs}$			30		
Gate-Drain Charge	$Q_{gd}$			16		
Gate Resistance	$R_g$		$f = 1 \text{ MHz}$	0.85	1.3	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 20 \text{ V}, R_L = 1.0 \Omega$ $I_D \geq 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		20	30	ns
Rise Time	$t_r$			11	17	
Turn-Off Delay Time	$t_{d(\text{off})}$			77	115	
Fall Time	$t_f$			10	15	
Turn-On Delay Time	$t_{d(\text{on})}$			102	155	
Rise Time	$t_r$	$V_{DD} = 20 \text{ V}, R_L = 1.0 \Omega$ $I_D \geq 20 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		62	95	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			180	270	
Fall Time	$t_f$			60	90	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$			110	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				200	
Body Diode Voltage	$V_{SD}$	$I_S = 20 \text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		50	75	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			70	105	nC
Reverse Recovery Fall Time	$t_a$			30		ns
Reverse Recovery Rise Time	$t_b$			20		

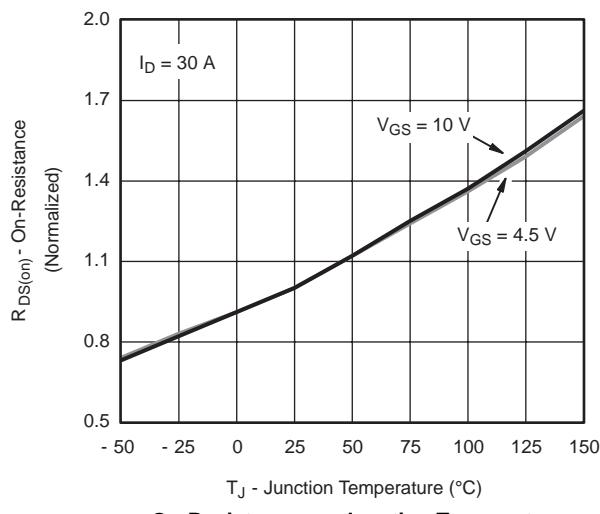
Notes:

a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

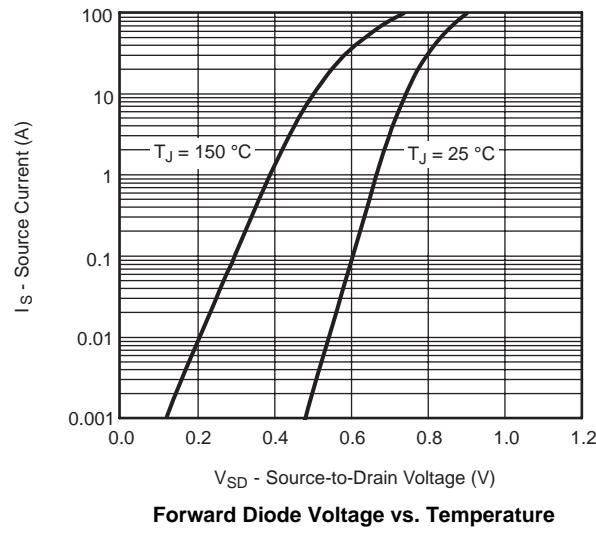
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

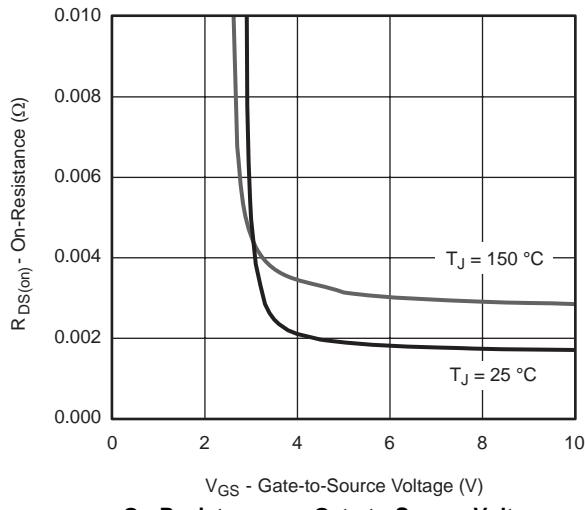
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


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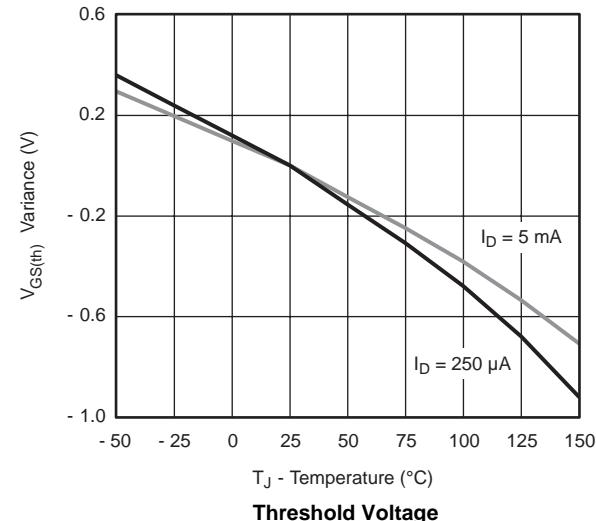
On-Resistance vs. Junction Temperature



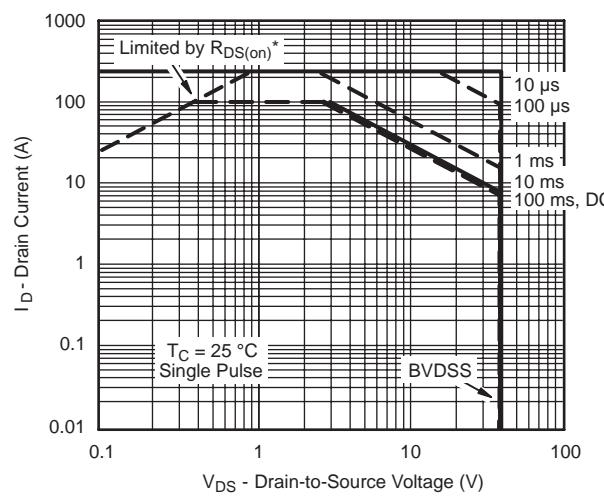
Forward Diode Voltage vs. Temperature



On-Resistance vs. Gate-to-Source Voltage

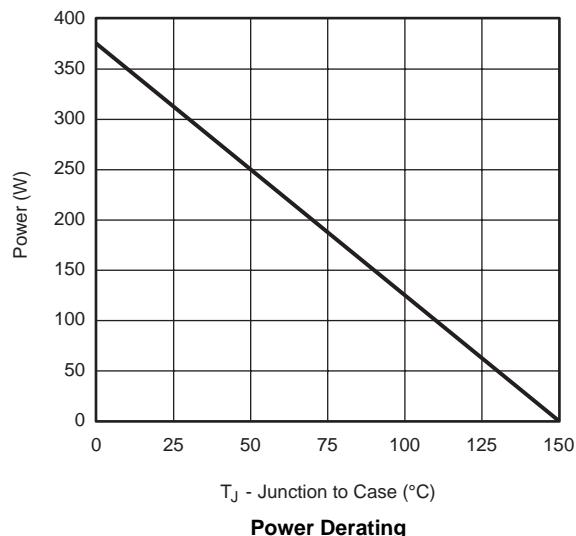
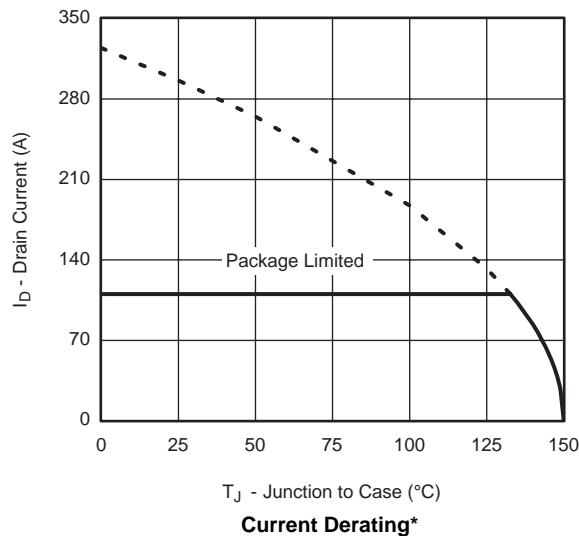


Threshold Voltage

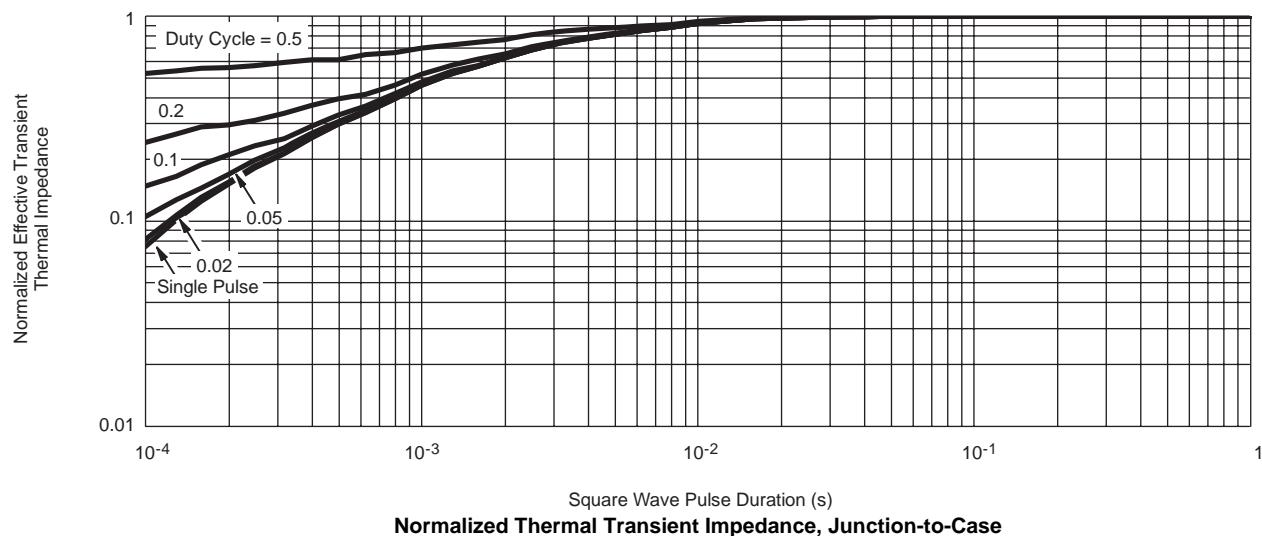


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

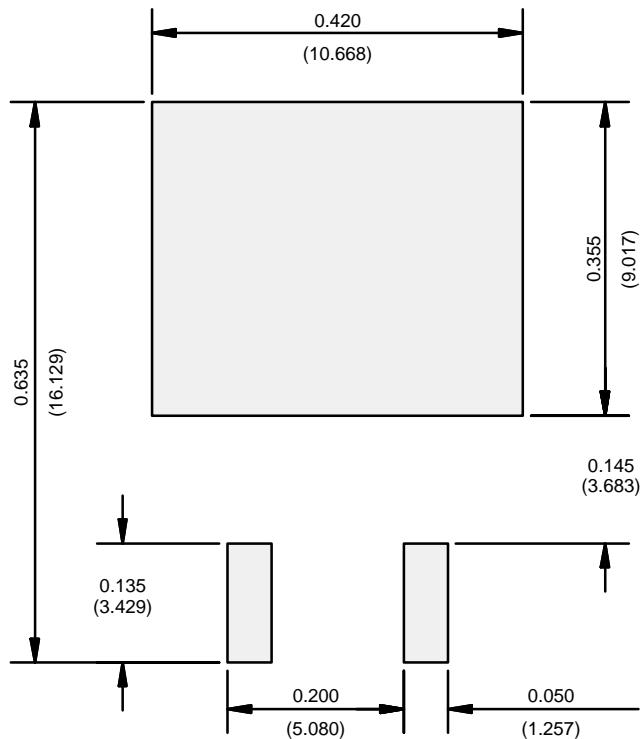
Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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